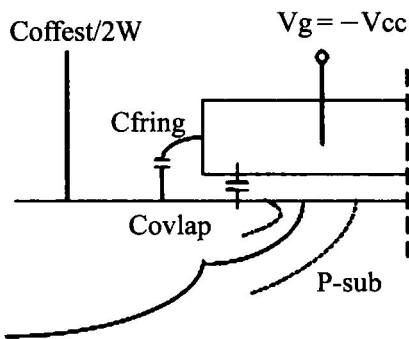


Accumulation Region

$$C_{acc} = 2C_{ovlap} + 2C_{fri} + C_{offse}/W$$



Inversion Region

$$C_{inv} = C_{gate} + 2C_{fri} + C_{offse}/W$$

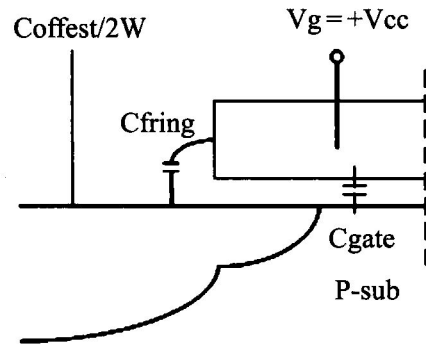
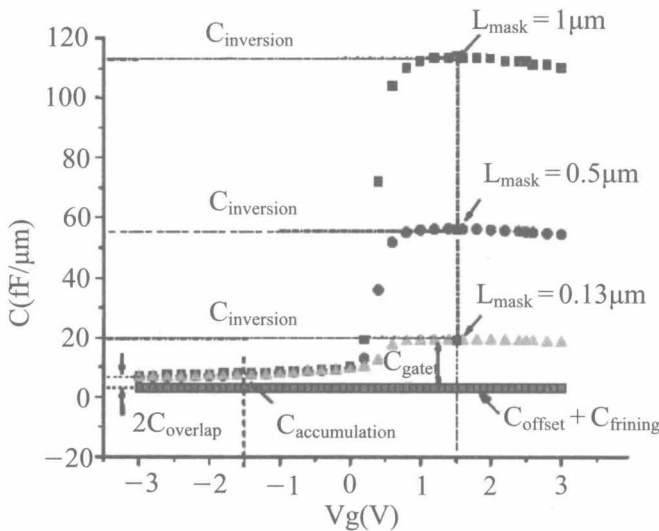


圖 13-44 分別於 accumulation 和 inversion 模式量測電容。



For NMOS device

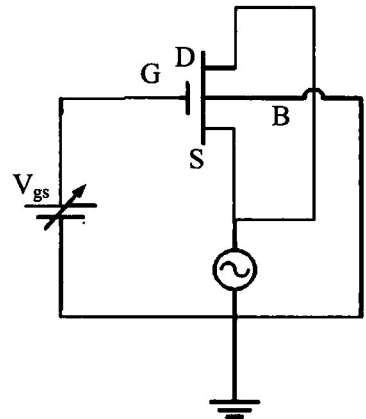


圖 13-45 利用電容法求 L_{eff} 的量測結果。

$$C_{inv1} = C_{gate1} + 2C_{fri1} + C_{offset1}/W$$

$$C_{inv2} = C_{gate2} + 2C_{fri2} + C_{offset2}/W$$

$$C_{fri} = \frac{2\epsilon_{ox}}{\pi} \ln \left[1 + \left(\frac{d_{gate}}{d_{ox, eff}} \right) \right]$$